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**Aqueous Dispersions, Process for their Production, and
their Use**

5 The present invention relates to the production of aqueous
dispersions that contain pyrogenically produced silicon
dioxide, a process for their production, and the use of the
dispersions for polishing semiconductor substrates.

10 Cerium oxide dispersions, obtained by calcining a cerium
compound followed by grinding of the oxide, have been used
for a long time for polishing glass. The dispersions have
particle sizes of more than 1000 nm and a high content of
impurities. They are suitable for the coarse polishing of
surfaces, but not for polishing sensitive optical surfaces,
semiconductor substrates or integrated circuits (chemical-
15 mechanical polishing, CMP).

20 Smaller cerium oxide particles are obtained by the so-
called hydrothermal synthesis. In this case a cerium(III)
salt is converted oxidatively under the influence of
temperature and pressure into cerium oxide, which
crystallises out in the form of fine particles. The
particle sizes of the cerium oxide obtained according to
this process are 80-100 nm (EP-A-947 469), 7-50 nm (US 5
389 352) or smaller than 30 nm and larger than 60 nm (US 5
772 780). The disadvantage of this method however is that
25 very dilute cerium(III) solutions have to be used as
starting materials.

30 Mixtures of cerium oxide and silicon dioxide produced by
the processes mentioned above are described in US 5 891
205. In this case the cerium oxide has to be deagglomerated
in a first step by means of a grinding mill. The cerium
oxide dispersion is then mixed in a second step with a
silicon dioxide dispersion based on silica sol and can be
used to planarize silicon discs.



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The disadvantage in this case is the complicated procedure and the costs involved in the production of this finely particulate dispersion. The deagglomeration of the cerium oxide using a grinding mill conceals the potential danger of the incorporation of impurities in the dispersion. Furthermore, it is known that silicon dioxide dispersions based on silica sol have a higher content of impurities than those based on pyrogenically produced silicon dioxide.

US 5 382 272 describes the activation of silicon dioxide particles by adsorption of a few weight percent, preferably 2 wt.%, of a cerium oxide or zirconium oxide dispersion. The particular feature of this process is that the activating effect is said to be obtained simply by grinding a silicon dioxide dispersion with a commercially available cerium oxide or zirconium oxide dispersion. The mixed dispersion that is thus obtained is said to behave like a pure cerium oxide dispersion when polishing semiconductor substrates with a high removal rate, but without leaving any scratches on the surface to be polished. Compared to the remaining processes in the prior art, the costs are minimal and the execution is simple. The particular disadvantages of this method are, as is also described in detail in WO 00/17 282 A1, the production of a dispersion having a narrow particle size range and the difficulty in achieving reproducible polishing results.

As the prior art shows, the extraordinarily high activity of cerium oxide compared to silicon dioxide and other dielectric oxides has excited a great deal of interest, mainly in the area of chemical-mechanical polishing (CMP).

The technical object of the invention is to provide an aqueous, cerium oxide-containing dispersion that can be produced simply, that contains only a small proportion of impurities, and in which the particle size can be reproducibly adjusted.

This technical object is achieved by using an aqueous dispersion containing pyrogenically produced silicon dioxide doped with cerium oxide, in which the cerium oxide is introduced through an aerosol of a cerium salt solution or suspension, and the mean particle size in the dispersion is less than 100 nm.

In the production of the silicon dioxide doped with cerium oxide a cerium salt solution or suspension is used as starting material, which is homogeneously mixed as an aerosol with the gaseous mixture obtained from the flame oxidation or flame hydrolysis of a volatile silicon compound such as for example silicon tetrachloride, hydrogen and oxygen. The aerosol/gaseous mixture is allowed to react in a flame. The resulting pyrogenically produced silicon dioxide doped by means of the aerosol is separated in a known manner from the gas stream.

As is described in detail in DE 196 50 500 A1, this production process leads to silicon dioxide particles doped with cerium oxide. The cerium oxide particles according to this process are always smaller than the silicon dioxide particles. This is an important prerequisite for the use of dispersions containing the cerium oxide-doped silicon dioxide particles for polishing applications, since otherwise scratches could be formed on the surface to be polished.

The dispersion has a good stability and is ideally suitable for polishing in the CMP sector. Good stability of the doped dispersion means that the time after which the viscosity of the dispersion increases or the dispersion gels or sediments is later than in the case of a dispersion containing a mixture of undoped silicon dioxide and cerium oxide.

As a result of the pyrogenic production process, in which as is known highly pure starting materials are used, the

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levels of impurities relevant for CMP applications are negligibly small.

With commercially obtained cerium oxide dispersions the cerium oxide is generally obtained from ores having a
5 relatively high content of impurities.

The degree of doping of the silicon dioxide produced by the above process may be varied within wide limits from 0.00001 up to 20 wt.%. When used for the production of an aqueous dispersion according to the present invention, the degree
10 of doping is preferably between 10 ppm and 10 wt.%, particularly preferably in the range between 300 ppm and 5 wt.%.

The BET surface of the cerium oxide-doped silicon dioxide is between 5 and 600 m²/g according to a preferred
15 embodiment of the invention. A range between 50 and 400 m²/g is particularly preferred. Within this range the dispersion exhibits a good stability.

The solids content of the dispersion containing cerium oxide-doped silicon dioxide is primarily governed by its
20 intended use. In order to reduce transportation costs a dispersion with the maximum possible solids content is aimed for, whereas for certain applications, such as for example the polishing of silicon discs, dispersions with low solids contents are used. A solids content of 0.1 to 70
25 wt.% is preferred according to the invention, the range between 1 and 30 wt.% being particularly preferred. In this range the cerium oxide-doped dispersion exhibits a good stability.

The dispersion may be used as such, for example for
30 polishing. The pH of this dispersion is between 3.5 and 4 depending on the degree of doping. The pH may however be varied in a wide pH range of ca. 3-11 by adding basically or acidically acting substances.

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An increase in the pH value may preferably be achieved by adding alkali hydroxides or amines. Ammonium hydroxide and potassium hydroxide are particularly preferred.

By adding acids the pH can be displaced to the acidic range down to pH 3. There are preferably used for this purpose carboxylic acids of the general formula $C_nH_{2n+1}CO_2H$ where $n=0-6$ or $n=8,10,12,14,16$, or dicarboxylic acids of the general formula $HO_2C(CH_2)_nCO_2H$ where $n=0-4$, or hydroxy-carboxylic acids of the general formula $R_1R_2C(OH)CO_2H$ where $R_1=H$, $R_2=CH_3$, CH_2CO_2H , $CH(OH)CO_2H$ or glycolic acid, pyruvic acid, salicylic acid or mixtures of the aforementioned acids. Acetic acid, citric acid and salicylic acid are particularly preferred for this purpose.

The present invention also provides a process for the production of the dispersion containing cerium oxide-doped silicon dioxide, which is characterised in that the cerium oxide-doped, pyrogenically produced silicon dioxide is dispersed in aqueous solution by means of a high energy input. Dispersion methods in which a sufficiently high energy input permits a dispersion of even extremely hard and highly aggregated materials are suitable for this purpose. Such methods include systems operating according to the rotor-stator principle, for example Ultra-Turrax machines, or agitator ball mills. Both systems however have a relatively low energy input. Significantly higher energy inputs are possible with a planetary kneader/mixer. The effectiveness of this system is however dependent on a sufficiently high viscosity of the processed mixture, in order to impart the high shear energies needed to separate the particles.

When grinding and dispersing doped oxide particles there is the danger that the doping substance will separate out during the grinding and dispersion. This leads to variable polishing results if the dispersion is to be used as a polishing agent in the CMP process.

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It has now been found that aqueous dispersions containing cerium oxide-doped silicon dioxide particles that are smaller than 100 nm and in which the doping substances has not separated out can be obtained by using high-pressure
5 homogenisers.

With these devices two pre-dispersed suspension streams under a pressure of up to 3500 kg/cm² are expanded through a diamond nozzle. Both dispersion jets strike one another exactly and the particles undergo a mutual grinding. In
10 another embodiment the pre-dispersion is also subjected to a high pressure, but in this case the particles collide against reinforced wall regions.

These devices have been used for a long time, among other things to disperse undoped oxides such as zinc oxide,
15 silicon dioxide or aluminium oxide (UK-A-2 063 695, EP-A-876 841, EP-A-773 270, WO 00/172 282 A1). The grinding and dispersion of doped oxides using these devices has not been described up to now.

The invention also provides for the use of the aqueous,
20 cerium oxide-doped dispersion for the chemical-mechanical polishing (CMP) of semiconductor substrates or layers applied to the latter. By using the cerium oxide-doped dispersion, a surface that is free of microscratches can be obtained at a high polishing rate.

25 The cerium oxide-doped dispersion according to the invention is particularly suitable for the final chemical-mechanical polishing in the shallow-trench isolation process (STI process), in which after applying a silicon nitride layer insulating structures are etched in the
30 silicon layer of a wafer, these cavities are then filled with silicon dioxide, and excess silicon dioxide is removed by chemical-mechanical polishing.

These dispersions are also suitable for the production of very finely particulate surface coatings in the paper-making industry or to produce special glasses.

5 Examples

Analytical process

The average secondary particle size was determined with a Zetasizer 3000 Hsa from the Malvern company.

(The surface of the powders that were used was determined by
10 the method of S. Brunauer, P. H. Emmet and I. Teller, J. Am. Chemical Society, Vol. 60, p. 309 (1938) and is generally termed the BET surface.

The viscosity of the dispersions that were produced was determined with a rotation rheometer, Model MCR 300, from
15 Physica and with a CC 27 measurement beaker. The viscosity value was measured at a shear rate of 100 1/sec. This shear rate is in a range in which the viscosity is practically independent of the shear stress.

(Sediment formation was evaluated by visual inspection in a
20 1000 ml capacity wide-necked polyethylene flask after a standing time of one week. Any sediment that may be present can easily be recognised by carefully tilting the flask.

The synthesis of the cerium oxide-doped silicon dioxide particles is carried out according to DE 196 50 500.

25 **Production of the dispersions**

Method A: 53 kg of fully deionised water and 80g of 30% KOH solution are placed in a 60 l stainless steel batch container. 8 kg of the particles according to Examples 1 to 8 are sucked in as a powder and coarsely pre-dispersed with
30 the aid of a disperser and suction mixer from Ystral (at

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4500 r.p.m.). After the introduction of the powder the dispersion is completed with a Type Z 66 rotor/stator throughflow homogeniser from Ystral with four processing crowns, a stator slit width of 1 mm, and a rotational speed of 11,500 r.p.m. During this 15-minute dispersion at 11,500 r.p.m. the pH is adjusted and maintained at a of 9.5 by adding further KOH solution. In this connection a further 96 g of KOH solution were used and an abrasive body concentration of 12.5 wt.% was adjusted by adding 2.8 kg of water.

Method B: about half the dispersion according to method A is ground with a "wet jet mill", Ultimaizer System from Sugino Machine Ltd., model HJP-25050, at a pressure of 250 MPa and with a diamond nozzle diameter of 0.3 mm and two grinding passes.

The analytical data of the dispersions are shown in Table 1.

Polishing process

Equipment: Presi Polisher Type 460 M, equipped with a 550 mm polishing table with a Rodel IC 1400 perforated polishing cloth.

Wafer: 4" silicon discs coated with 500 nm SiO₂ (thermally produced), 4" silicon discs coated with 500 nm Si₃N₄ (LPCVD).

Polishing parameters:

Polishing duration/polishing pressure: 15 secs./0.2 bar, 60 secs./0.8 bar,
15 secs./0.2 bar, with rinsing
Rotational velocity 60 rpm (both)
Metering rate of the dispersion: 100 ml/min.
Temperature: ca. 25°C

Preliminary treatment: treatment with a diamond-tipped grinding head disc at a pressure of 1 bar for 10 secs. before each polishing test.

5 Post CMP cleaning is carried out by ultrasonic cleaning (Techsonic) and using a SVG 8620 brush-type cleaner (single side cleaner/dryer).

(The evaluation of the abrasion performance (removal rate, RR) is carried out by measuring the layer thickness using a Prometrix FDT 650 device (KLA-Tencor Corporation) and by
10 weighing the wafer on a Sartorius BP 210D scales. 10 wafers were polished and evaluated in each case to determined the mean RR.

Large scratches and defects were evaluated with a Surfscan Model 5000 device from Tencor.

15 The values for the abrasion performances and the selectivities of the dispersions according to Examples 1 to 8 are summarised in Table 2

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Table 1: Analytical data of the dispersions obtained according to Examples 1 to 8

Example	Method	CeO ₂ - Doping [wt. %]	BET- Surface [m ² /g]	Mean Particle Diameter (Number) [nm]	Mean Particle Diameter (Volume) [nm]	Viscosity [mPa.s]	Deposit
1	A	none*	90	197	271	7	yes
2	B	none*	90	150	163	3	no
3	A	0.11	83	185	251	3	yes
4	B	0.11	83	84	96	2	no
5	A	0.34	79	190	257	3	yes
6	B	0.34	79	78	92	2	no
7	A	0.71	81	181	261	3	yes
8	B	0.71	81	91	99	2	no

* Aerosil 90, Degussa AG.

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Table 2: Mean removal rates (RR) and SiO₂/Si₃N₄ selectivities of the dispersions produced according to Examples 1 to 8

Exam- ples	Thermal SiO ₂		Si ₃ N ₄		Selectivity RR SiO ₂ /RR Si ₃ N ₄		Scratches/ Defects
	weighing [nm/min]	Prometrix [nm/min]	weighing [nm/min]	Prometrix [nm/min]	weighing	Prometrix	
1	1078	1005	325	303	3.3	3.4	some
2	1023	956	321	313	3.3	3.3	none
3	1153	1072	331	315	3.5	3.4	a few
4	1197	1021	339	293	3.5	3.5	none
5	1337	1275	311	298	4.3	4.3	a few
6	1297	1226	299	292	4.3	4.2	none
7	1627	1558	316	310	5.1	5.0	a few
8	1580	1506	305	308	5.2	4.9	none

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Patent Claims

1. Aqueous dispersion, characterised in that it contains a cerium oxide-doped, pyrogenically produced silicon dioxide, wherein the cerium oxide is introduced through an aerosol of a cerium salt solution or suspension and the average particle size in the dispersion is less than 100 nm.
2. Aqueous dispersion according to claim 1, characterised in that the cerium content of the doped silicon dioxide is between 10 ppm and 10 wt.%.
3. Aqueous dispersion according to claim 1 or 2, characterised in that the BET surface of the cerium oxide-doped silicon dioxide is between 5 and 600 m²/g.
4. Aqueous dispersion according to any of claims 1 to 3, characterised in that the solids content in the dispersion is between 0.1 and 70 wt.%.
5. Aqueous dispersion according to any of claims 1 to 4, characterised in that the pH value of the dispersion is between 3 and 11.
6. Aqueous dispersion according to any of claims 1 to 5, characterised in that the pH value is adjusted using amines or alkali hydroxides.
7. Aqueous dispersion according to any of claims 1 to 5, characterised in that the pH value is adjusted using carboxylic acids of the general formula $C_nH_{2n+1}CO_2H$, where $n=0-6$ or $n=8,10,12,14,16$, or dicarboxylic acids of the general formula $HO_2C(CH_2)_nCO_2H$, where $n=0-4$, or hydroxycarboxylic acids of the general formula $R_1R_2C(OH)CO_2H$, where $R_1=H$, $R_2=CH_3$, CH_2CO_2H , $CH(OH)CO_2H$ or glycolic acid, pyruvic acid, salicylic acid or mixtures thereof.

8. Process for the production of an aqueous dispersion according to any of claims 1 to 7, characterised in that the cerium oxide-doped, pyrogenically produced silicon dioxide is dispersed in aqueous solution by means of a high energy input.
9. Process for the production of an aqueous dispersion according to claim 8, characterised in that for the grinding and dispersion of a cerium oxide-doped silicon dioxide in an aqueous solvent, a device is used in which the particles to be dispersed are under a pressure of up to 3500 kg/cm^2 , are expanded through a nozzle, and collide with one another or against wall regions of the device.
10. Use of the aqueous dispersion according to any of claims 1 to 7 for the chemical-mechanical polishing of semiconductor substrates or of layers applied thereto.
11. Use of the aqueous dispersion according to any of claims 1 to 7 for producing finely particulate surface coatings in the paper industry.
12. Use of the aqueous dispersion according to any of claims 1 to 7 for producing special glasses.